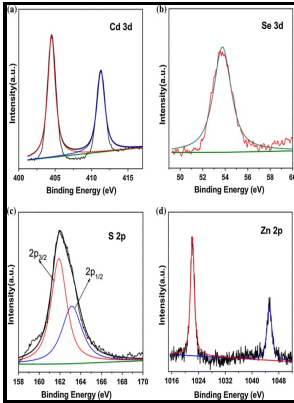


Preparation and the physical properties of CdSe-Ge heterojunctions.

University of Salford - Blue emission at atomically sharp 1D heterojunctions between graphene and h



Description: -

-Preparation and the physical properties of CdSe-Ge heterojunctions.

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Notes: PhD thesis, Electrical Engineering.

This edition was published in 1969



Filesize: 70.33 MB

Tags: #Blue #emission #at #atomically #sharp #1D #heterojunctions #between #graphene #and #h

Facile one

CdS films, 2 microns thick, are produced by evaporating CdS powder from a baffled source onto glass or molybdenum-foil substrates which are heated up to 180-C in a vacuum of 1×10^{-j} torr. The large positive MR is a characteristic of the inhomogeneous semiconductors and p-n junctions

»»»»

First principles study on planar mechanism and heterostructures of ultraflat stanene

Nanotechnology 2005, 16 10 , 2100-2103.

Large rectification magnetoresistance in nonmagnetic Al/Ge/Al heterojunctions

Figure shows an SEM image of the circular graphene region embedded in the h-BN monolayer, confirming a clear boundary between the graphene and h-BN regions. Electronic states at the graphene—hexagonal boron nitride zigzag interface. Enhanced low field magnetoresistance in germanium and silicon-diode combined devices at room temperature.

Preparation and characterization of Cu:Co3O4/Si heterojunction prepared by spray pyrolysis

Chemical vapor deposition and etching of high-quality monolayer hexagonal boron nitride films. Magnetically induced impurity banding in n-InSb.

Two

The most intriguing and innovative part of present investigation is the observation of greatly enhanced rectification MR as shown in. The carbided chromium layers possess high electrical conductivity and a high coefficient in the infrared region of spectrum.

Enhanced ammonia sensing properties of rGO/WS2 heterojunction based chemiresistive sensor by marginal sulfonate decoration

Compared with other 2D materials, 2D Xenes have the tunable layer-dependent bandgaps, leading to the potential of bridging the bandgap space between graphene zero bandgap, Mxenes limited bandgaps, TMDs large bandgaps, and h-BN insulator. Using giant magnetoresistance stripes to efficiently generate direct voltage signals from alternating current excitations.

Two

G Babonas and A Sileika, *P_hys Stat Sol*, 42 2, Dec 1970. To understand the mechanism of blue PL emission at 410 nm, we performed PL measurements on several control samples.

Blue emission at atomically sharp 1D heterojunctions between graphene and h

M1 and M2 are also high-reflection-coated at the wavelength of 1000—1100 nm with the curvature radius of 800 and 200 mm, respectively. Extremely large magnetoresistance in boron-doped silicon. *Journal of Colloid and Interface Science* 2005, 287 2, 664-670.

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